

**GigaMOS™**  
**Power MOSFET**
**IXFN160N30T**

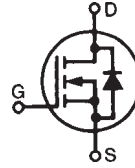
$$V_{DSS} = 300V$$

$$I_{D25} = 130A$$

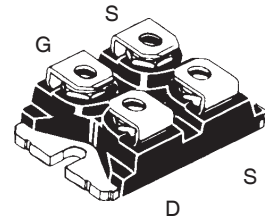
$$R_{DS(on)} \leq 19m\Omega$$

$$t_{rr} \leq 200ns$$

N-Channel Enhancement Mode  
 Avalanche Rated  
 Fast Intrinsic Diode



miniBLOC, SOT-227  
 E153432



G = Gate      D = Drain  
 S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source ( Gate Return ) Terminal.

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	300	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	300	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	130	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	440	A
$I_A$	$T_C = 25^\circ C$	40	A
$E_{AS}$	$T_C = 25^\circ C$	3	J
$dV/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	20	V/ns
$P_D$	$T_C = 25^\circ C$	900	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$V_{ISOL}$	50/60 Hz, RMS $t = 1$ minute	2500	V~
	$I_{ISOL} \leq 1mA$ $t = 1$ second	3000	V~
$M_d$	Mounting Torque	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
<b>Weight</b>		30	g

**Features**

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Isolation voltage 2500 V~
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low  $R_{DS(on)}$

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- DC-DC Converters
- Battery Chargers
- Switched-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies
- High Speed Power Switching Applications

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 3mA$	300		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8mA$	2.5		5.0 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			50 $\mu A$ 3 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 60A$ , Note 1			19 m $\Omega$

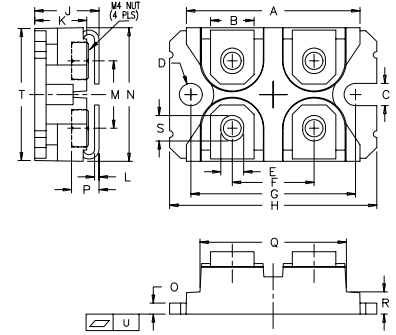
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 60\text{A}$ , Note 1	100	160	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		28	nF
$C_{oss}$			1770	pF
$C_{rss}$			125	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 15\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 80\text{A}$ $R_G = 1\Omega$ (External)		37	ns
$t_r$			38	ns
$t_{d(off)}$			105	ns
$t_f$			25	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 80\text{A}$		335	nC
$Q_{gs}$			123	nC
$Q_{gd}$			56	nC
$R_{thJC}$			0.138	$^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			160 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			640 A
$V_{SD}$	$I_F = 60\text{A}, V_{GS} = 0\text{V}$ , Note 1			1.3 V
$t_{rr}$	$I_F = 80\text{A}, V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 75\text{V}$		1.09	200 ns
$Q_{RM}$				$\mu\text{C}$
$I_{RM}$			13	A

Note 1: Pulse Test,  $t \leq 300\mu\text{s}$ ; Duty Cycle,  $d \leq 2\%$ .

### SOT-227B (IXFN) Outline



(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

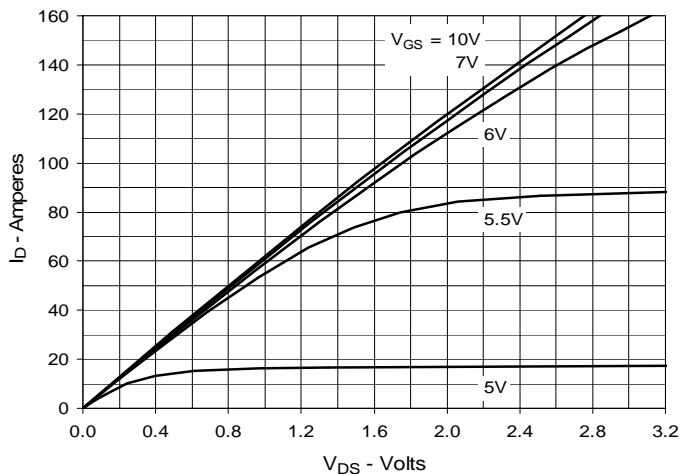
### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

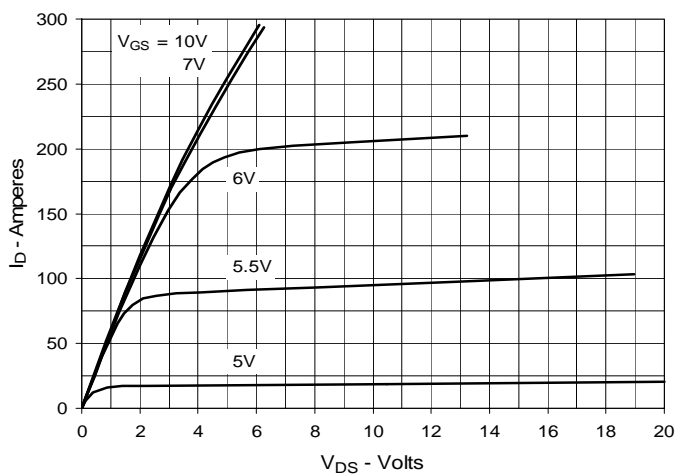
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

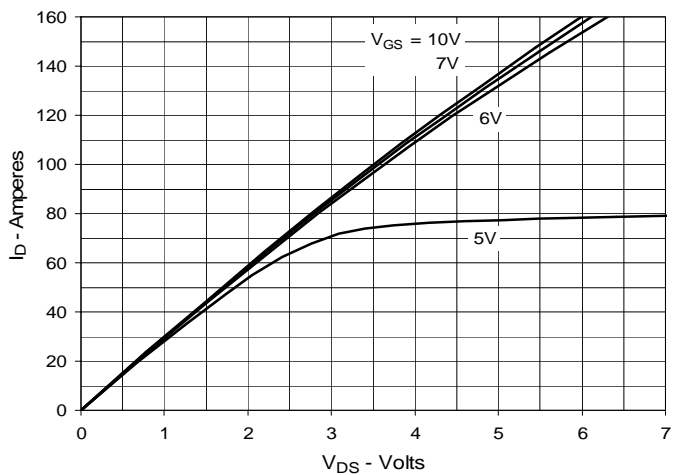
**Fig. 1. Output Characteristics @ 25°C**



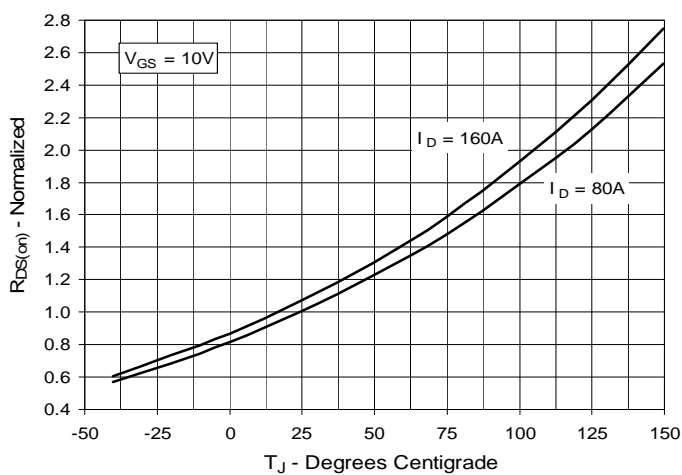
**Fig. 2. Extended Output Characteristics @ 25°C**



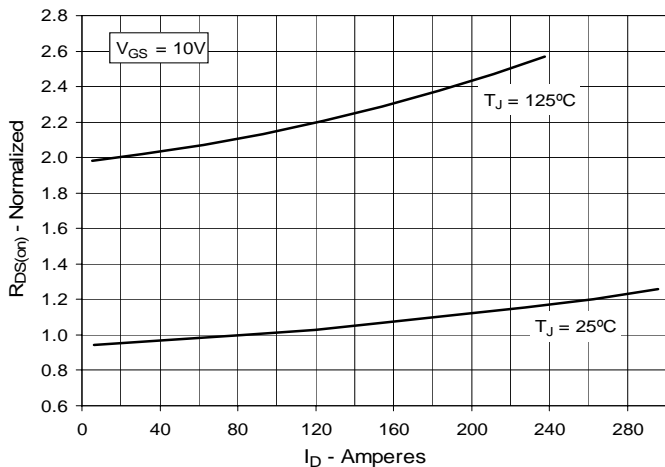
**Fig. 3. Output Characteristics @ 125°C**



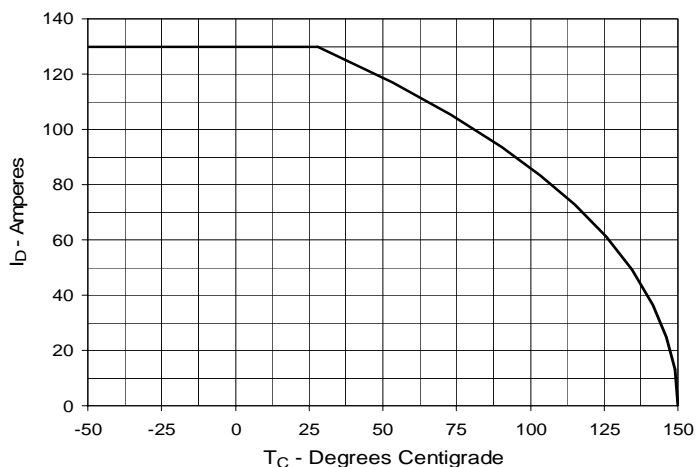
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 80A$  Value vs. Junction Temperature**



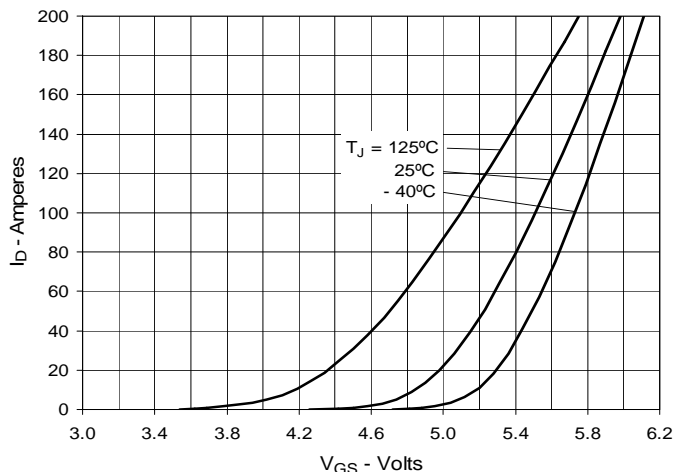
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 80A$  Value vs. Drain Current**



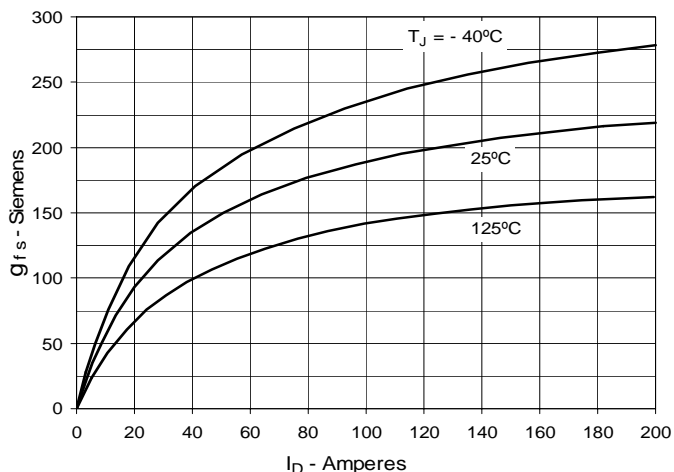
**Fig. 6. Maximum Drain Current vs. Case Temperature**



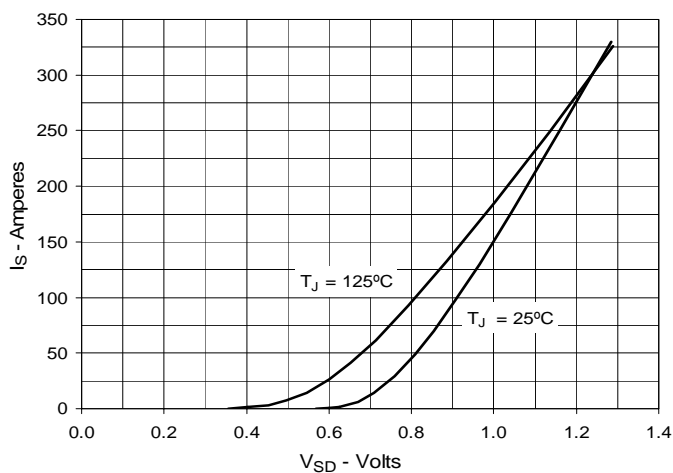
**Fig. 7. Input Admittance**



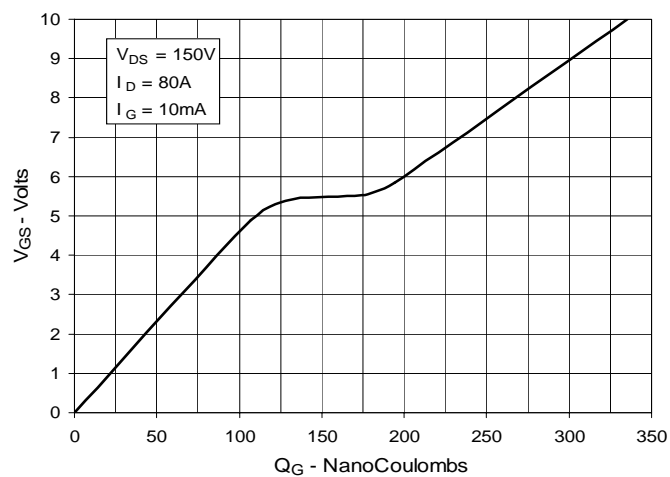
**Fig. 8. Transconductance**



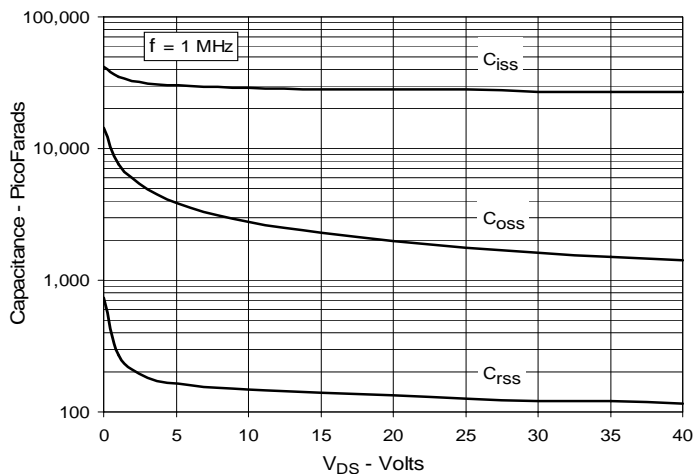
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**

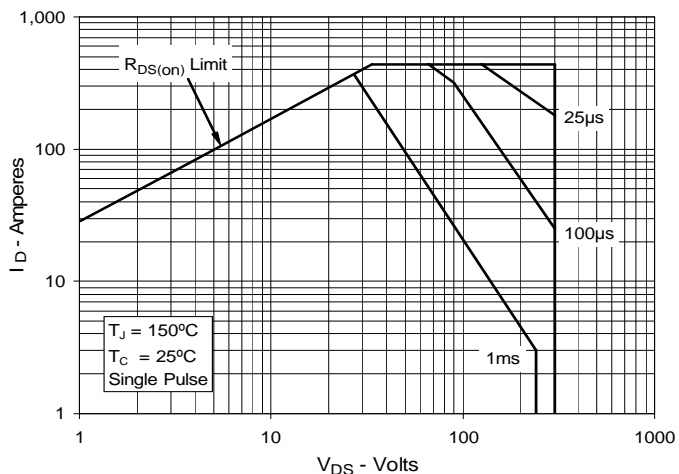


Fig. 13. Maximum Transient Thermal Impedance

